D16:SiliconB
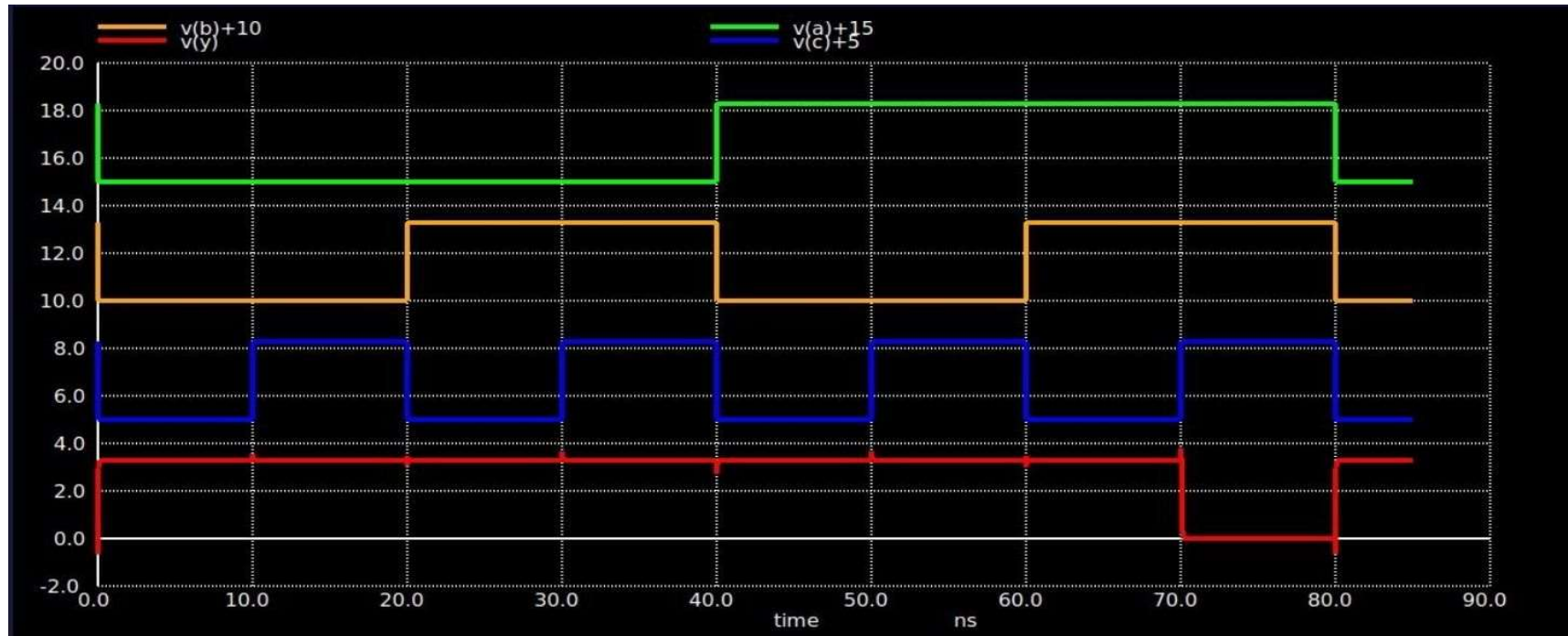

NAND3_1 FUNCTIONAL SIMULATION RESULTS

D16:SiliconB

Input Pin	Output	When Condition	Tin (ns)	Out Load (pF)	Delay (ns)	Tout (ns)
C(LH)	Y(HL)	A&B	0.0100	0.0010	0.0433	0.0748
C(HL)	Y(LH)	A&B	0.0100	0.0010	0.0752	0.0972
B(LH)	Y(HL)	A&C	0.0100	0.0010	0.0387	0.0587
B(HL)	Y(LH)	A&C	0.0100	0.0010	0.0681	0.0972
A(LH)	Y(HL)	B&C	0.0100	0.0010	0.0288	0.0442
A(HL)	Y(LH)	B&C	0.0100	0.0010	0.0545	0.0965

NAND3_1 TIMING SIMULATION RESULTS

IEEE

D16:SiliconB

When Condition	Power(nW)
!A&!B&!C	0.0112
!A&!B&C	0.0112
!A&B&!C	0.0113
!A&B&C	0.0117
A&!B&!C	0.0291
A&!B&C	0.0294
A&B&!C	0.0469
A&B&C	0.0338

NAND3_1 LEAKAGE POWER CONSUMPTION

D16:SiliconB
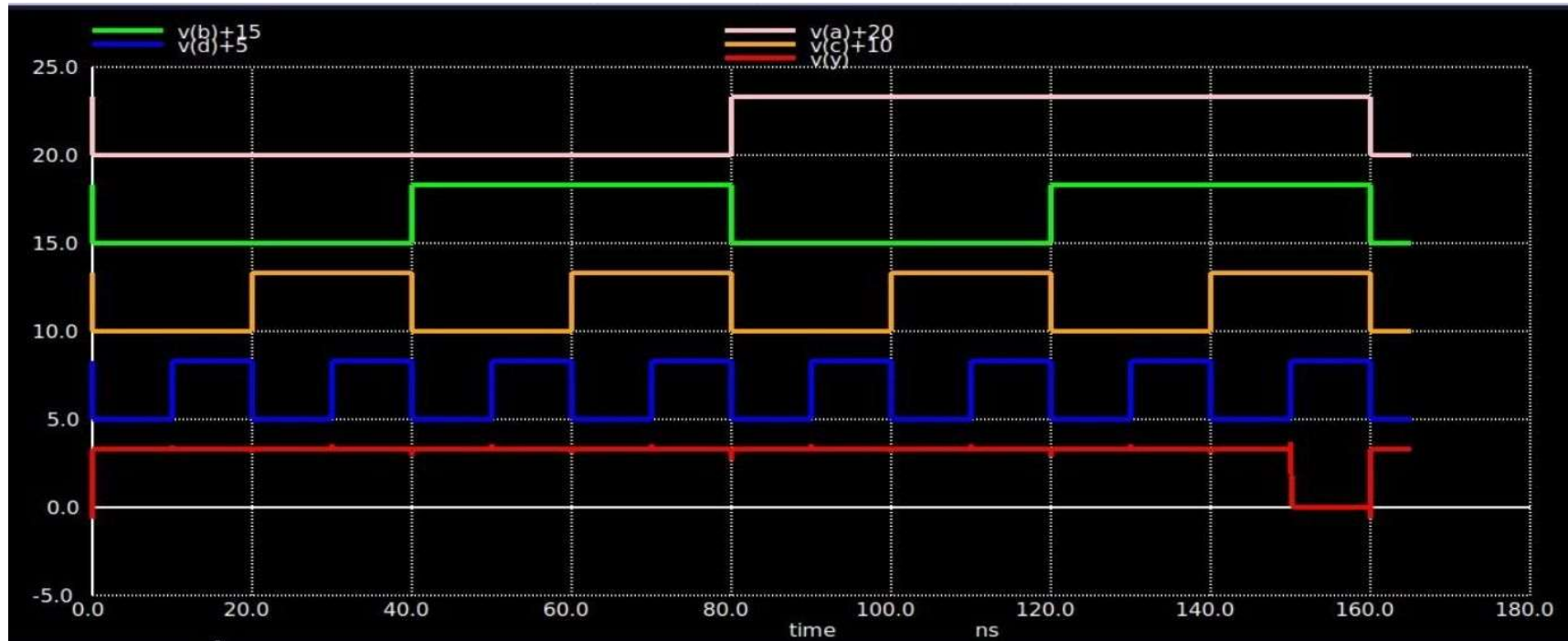
NAND4_1 FUNCTIONAL SIMULATION RESULTS

D16:SiliconB

Input Pin	Output	When Condition	Tin (ns)	Out Load(pF)	Delay (ns)	Tout (ns)
C(LH)	Y(HL)	A&B&D	0.0100	0.0010	0.0485	0.1583
C(HL)	Y(LH)	A&B&D	0.0100	0.0010	0.1109	0.0832
B(LH)	Y(HL)	A&C&D	0.0100	0.0010	0.0426	0.1581
B(HL)	Y(LH)	A&C&D	0.0100	0.0010	0.0966	0.0669
A(LH)	Y(HL)	B&C&D	0.0100	0.0010	0.0332	0.1558
A(HL)	Y(LH)	B&C&D	0.0100	0.0010	0.0745	0.0526
D(LH)	D(HL)	A&B&C	0.0100	0.0010	0.0449	0.1583
D(HL)	D(LH)	A&B&C	0.0100	0.0010	0.1817	0.0980

NAND4_1 TIMING SIMULATION RESULTS

D16:SiliconB

When Condition	Power(nW)
!A&!B&!C&!D	0.0112
!A&!B&!C&D	0.0112
!A&!B&C&!D	0.0112
!A&!B&C&D	0.0112
!A&B&!C&!D	0.0113
!A&B&!C&D	0.0113
!A&B&C&!D	0.0114
!A&B&C&D	0.0117

When Condition	Power(nW)
A&!B&!C&!D	0.0291
A&!B&!C&D	0.0291
A&!B&C&!D	0.0292
A&!B&C&D	0.0294
A&B&!C&!D	0.0467
A&B&!C&D	0.0469
A&B&C&!D	0.0643
A&B&C&D	0.0445

NAND4_1 LEAKAGE POWER CONSUMPTION